MC14012B

B-Suffix Series CMOS Gates

The B Series logic gates are constructed with P−Channel and N−Channel enhancement mode devices in a single monolithic structure (Complementary MOS). Their primary use is where low power dissipation and/or high noise immunity is desired.

Features

- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- All Outputs Buffered
- Capable of Driving Two Low−Power TTL Loads or One Low−Power Schottky TTL Load Over the Rated Temperature Range
- Double Diode Protection on All Inputs
- Pin−for−Pin Replacements for Corresponding CD4000 Series B Suffix Devices
- Pb−Free Packages are Available*

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	−0.5 to +18.0	V
V_{in}, V_{out}	Input or Output Voltage Range (DC or Transient)	−0.5 to V_{DD} + 0.5	V
I_{in}, I_{out}	Input or Output Current (DC or Transient) per Pin	±10	mA
P_D	Power Dissipation, per Package (Note 1)	500	mW
T_A	Ambient Temperature Range	−55 to +125	°C
T_{stg}	Storage Temperature Range	−65 to +150	°C
T_L	Lead Temperature (8−Second Soldering)	260	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Temperature Derating:
   Plastic “P and D/DW” Packages: – 7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high−impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \le (V_{in}$ or $V_{out}) \le V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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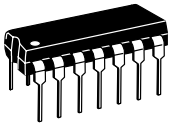
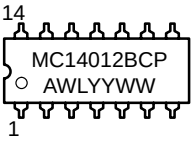
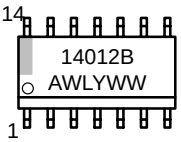
MARKING DIAGRAMS

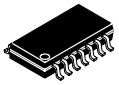


PDIP−14
P SUFFIX
CASE 646

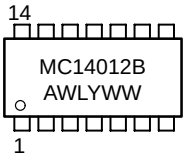


SOIC−14
D SUFFIX
CASE 751A





SOEIAJ−14
F SUFFIX
CASE 965

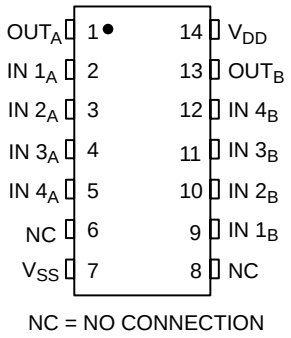


A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week

ORDERING INFORMATION

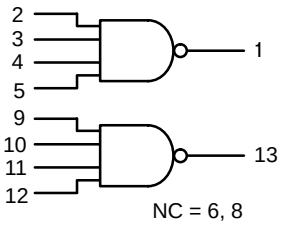
See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MC14012B
Dual 4−Input NAND Gate



NC = NO CONNECTION

Figure 1. Pin Assignment



NC = 6, 8

V_{DD} = PIN 14
V_{SS} = PIN 7

Figure 2. Logic Diagram

ORDERING INFORMATION

Device	Package	Shipping†
MC14012BCP	PDIP−14	500 Units / Rail
MC14012BCPG	PDIP−14 (Pb−Free)	500 Units / Rail
MC14012BD	SOIC−14	55 Units / Rail
MC14012BDG	SOIC−14 (Pb−Free)	55 Units / Rail
MC14012BDR2	SOIC−14	2500 Units / Tape & Reel
MC14012BDR2G	SOIC−14 (Pb−Free)	2500 Units / Tape & Reel
MC14012BFEL	SOEIAJ−14	2000 Units / Tape & Reel
MC14012BFELG	SOEIAJ−14 (Pb−Free)	2000 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V_{DD} Vdc	− 55°C Min	− 55°C Max	25°C Min	25°C Typ (Note 2)	25°C Max	125°C Min	125°C Max	Unit
Output Voltage “0” Level V_{in} = V_{DD} or 0	V_{OL}	5.0 10 15	− − −	0.05 0.05 0.05	− − −	0 0 0	0.05 0.05 0.05	− − −	0.05 0.05 0.05	Vdc
“1” Level V_{in} = 0 or V_{DD}	V_{OH}	5.0 10 15	4.95 9.95 14.95	− − −	4.95 9.95 14.95	5.0 10 15	− − −	4.95 9.95 14.95	− − −	Vdc
Input Voltage “0” Level (V_O = 4.5 or 0.5 Vdc) (V_O = 9.0 or 1.0 Vdc) (V_O = 13.5 or 1.5 Vdc)	V_{IL}	 5.0 10 15	 − − −	 1.5 3.0 4.0	 − − −	 2.25 4.50 6.75	 1.5 3.0 4.0	 − − −	 1.5 3.0 4.0	Vdc
“1” Level (V_O = 0.5 or 4.5 Vdc) (V_O = 1.0 or 9.0 Vdc) (V_O = 1.5 or 13.5 Vdc)	V_{IH}	 5.0 10 15	 3.5 7.0 11	 − − −	 3.5 7.0 11	 2.75 5.50 8.25	 − − −	 3.5 7.0 11	 − − −	Vdc
Output Drive Current (V_{OH} = 2.5 Vdc) Source (V_{OH} = 4.6 Vdc) (V_{OH} = 9.5 Vdc) (V_{OH} = 13.5 Vdc)	I_{OH}	 5.0 5.0 10 15	 – 3.0 – 0.64 – 1.6 – 4.2	 − − − −	 – 2.4 – 0.51 – 1.3 – 3.4	 – 4.2 – 0.88 – 2.25 – 8.8	 − − − −	 – 1.7 – 0.36 – 0.9 – 2.4	 − − − −	mAdc
(V_{OL} = 0.4 Vdc) Sink (V_{OL} = 0.5 Vdc) (V_{OL} = 1.5 Vdc)	I_{OL}	5.0 10 15	0.64 1.6 4.2	− − −	0.51 1.3 3.4	0.88 2.25 8.8	− − −	0.36 0.9 2.4	− − −	mAdc
Input Current	I_{in}	15	−	± 0.1	−	±0.00001	± 0.1	−	± 1.0	μAdc
Input Capacitance (V_{in} = 0)	C_{in}	−	−	−	−	5.0	7.5	−	−	pF
Quiescent Current (Per Package)	I_{DD}	5.0 10 15	− − −	0.25 0.5 1.0	− − −	0.0005 0.0010 0.0015	0.25 0.5 1.0	− − −	7.5 15 30	μAdc
Total Supply Current (Notes 3, 4) (Dynamic plus Quiescent, Per Gate, C_L = 50 pF)	I_T	5.0 10 15	I_T = (0.3 μA/kHz) f + I_{DD}/N I_T = (0.6 μA/kHz) f + I_{DD}/N I_T = (0.9 μA/kHz) f + I_{DD}/N							μAdc

2. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.
3. The formulas given are for the typical characteristics only at 25°C.
4. To calculate total supply current at loads other than 50 pF:

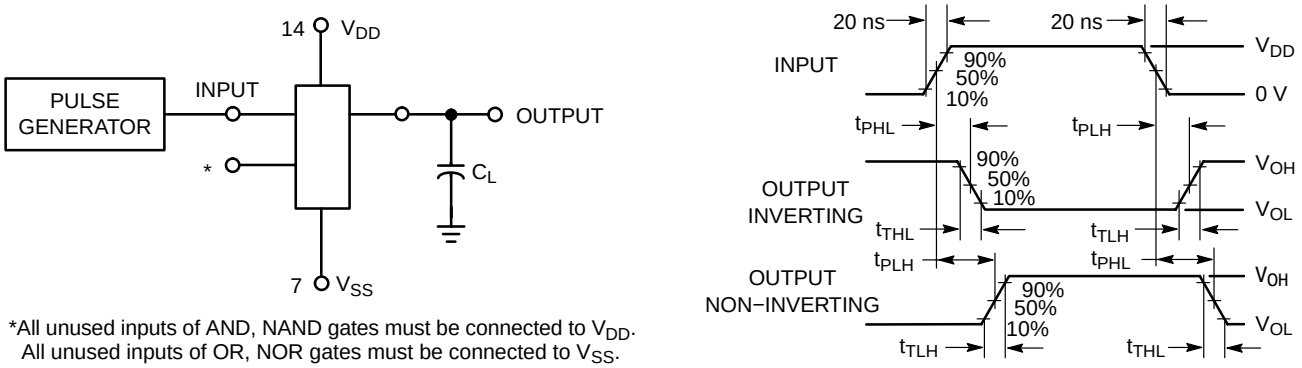
$$I_T(C_L) = I_T(50\ pF) + (C_L - 50)\ Vfk$$

where: I_T is in μA (per package), C_L in pF, V = (V_{DD} − V_{SS}) in volts, f in kHz is input frequency, and k = 0.001 x the number of exercised gates per package.

SWITCHING CHARACTERISTICS (Note 5) (C_L = 50 pF, T_A = 25°C)

Characteristic	Symbol	V_{DD} Vdc	Min	Typ (Note 6)	Max	Unit
Output Rise Time	t_{TLH}					ns
t_{TLH} = (1.35 ns/pF) C_L + 33 ns		5.0	–	100	200	
t_{TLH} = (0.60 ns/pF) C_L + 20 ns		10	–	50	100	
t_{TLH} = (0.40 ns/PF) C_L + 20 ns		15	–	40	80	
Output Fall Time	t_{THL}					ns
t_{THL} = (1.35 ns/pF) C_L + 33 ns		5.0	–	100	200	
t_{THL} = (0.60 ns/pF) C_L + 20 ns		10	–	50	100	
t_{THL} = (0.40 ns/pF) C_L + 20 ns		15	–	40	80	
Propagation Delay Time	t_{PLH}, t_{PHL}					ns
t_{PLH}, t_{PHL} = (0.90 ns/pF) C_L + 115 ns		5.0	–	160	300	
t_{PLH}, t_{PHL} = (0.36 ns/pF) C_L + 47 ns		10	–	65	130	
t_{PLH}, t_{PHL} = (0.26 ns/pF) C_L + 37 ns		15	–	50	100	

5. The formulas given are for the typical characteristics only at 25°C.
6. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.



*All unused inputs of AND, NAND gates must be connected to V_{DD}.
All unused inputs of OR, NOR gates must be connected to V_{SS}.

Figure 3. Switching Time Test Circuit and Waveforms

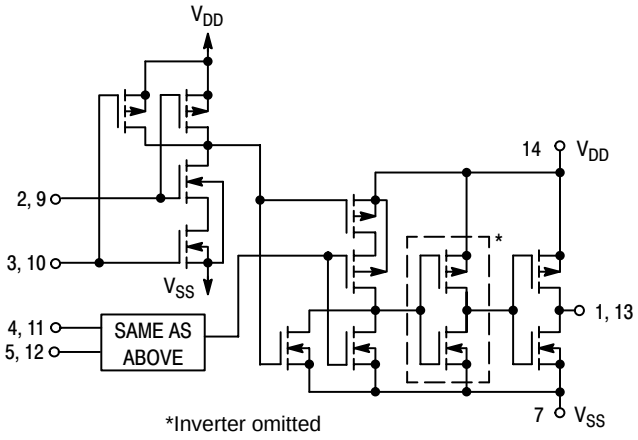


Figure 4. Circuit Schematic − One of Two Gates Shown

TYPICAL B−SERIES GATE CHARACTERISTICS

N−CHANNEL DRAIN CURRENT (SINK)

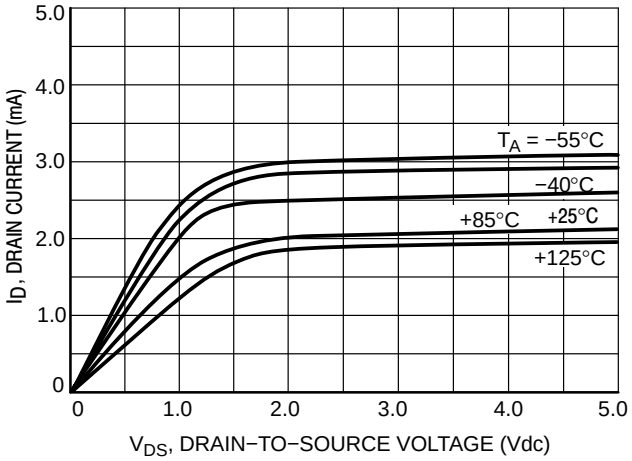


Figure 5. V_{GS} = 5.0 Vdc

P−CHANNEL DRAIN CURRENT (SOURCE)

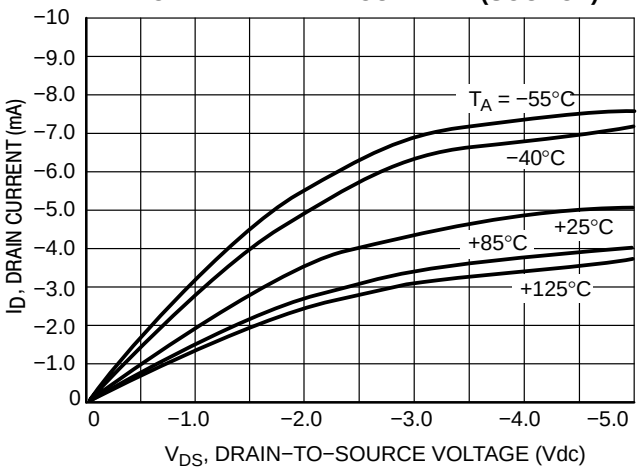


Figure 6. V_{GS} = − 5.0 Vdc

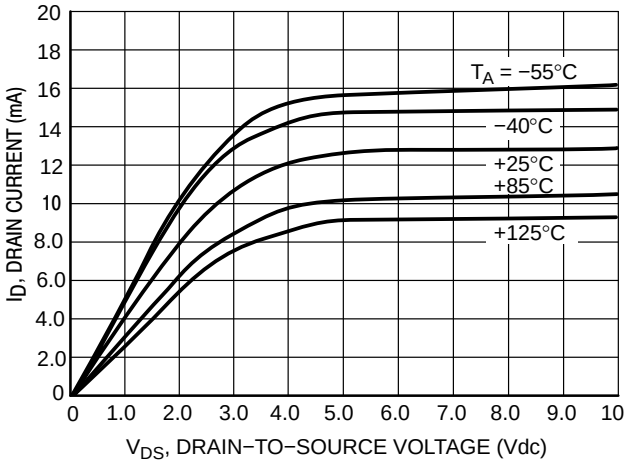


Figure 7. V_{GS} = 10 Vdc

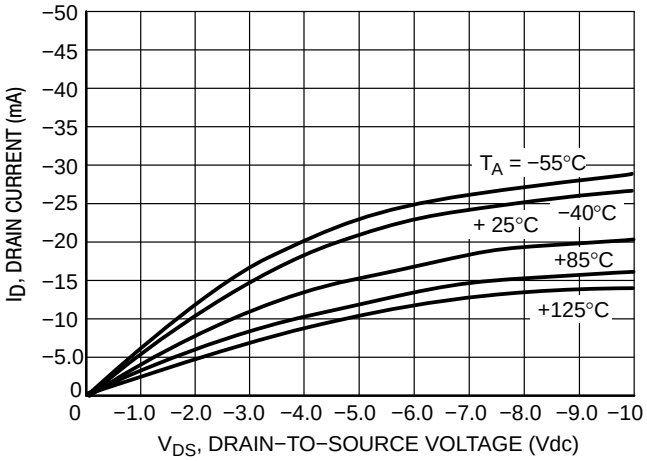


Figure 8. V_{GS} = − 10 Vdc

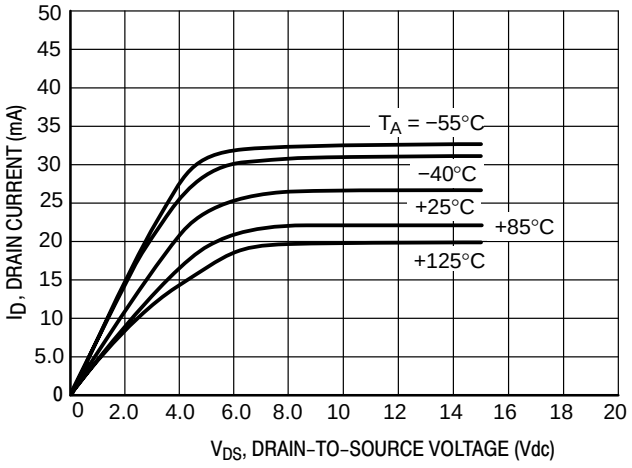


Figure 9. V_{GS} = 15 Vdc

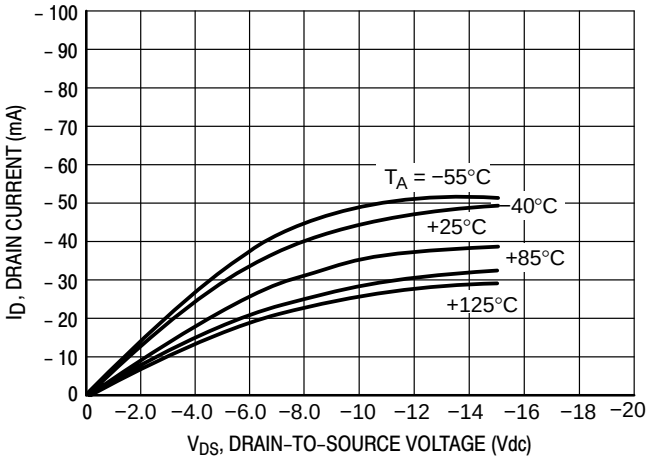


Figure 10. V_{GS} = − 15 Vdc

These typical curves are not guarantees, but are design aids.
Caution: The maximum rating for output current is 10 mA per pin.

VOLTAGE TRANSFER CHARACTERISTICS

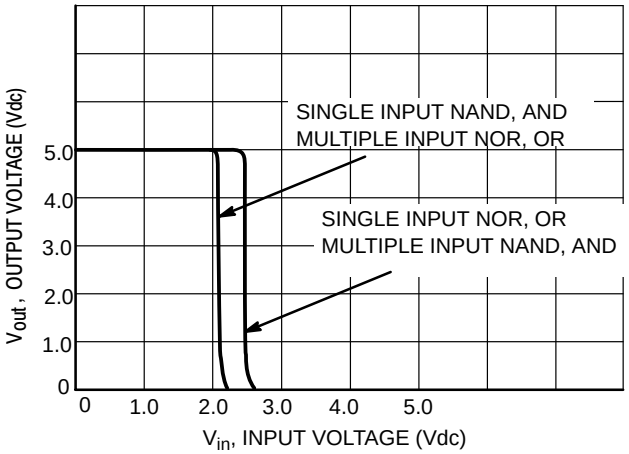


Figure 11. V_{DD} = 5.0 Vdc

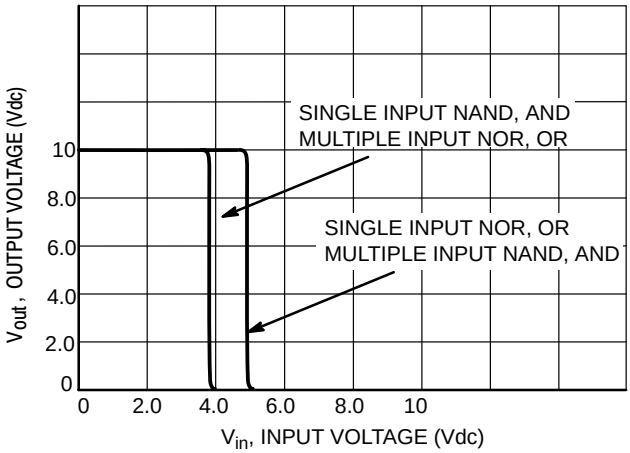


Figure 12. V_{DD} = 10 Vdc

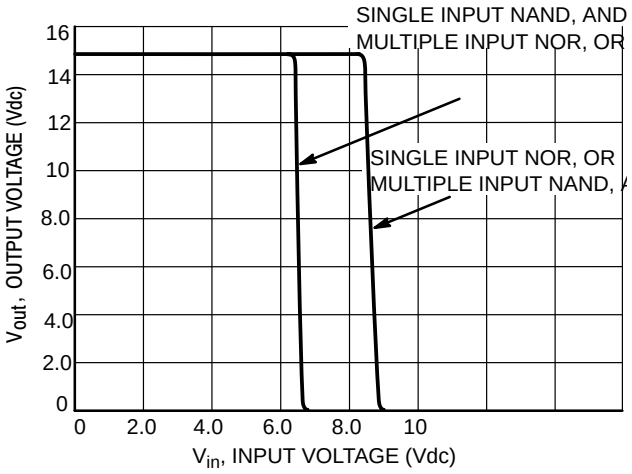


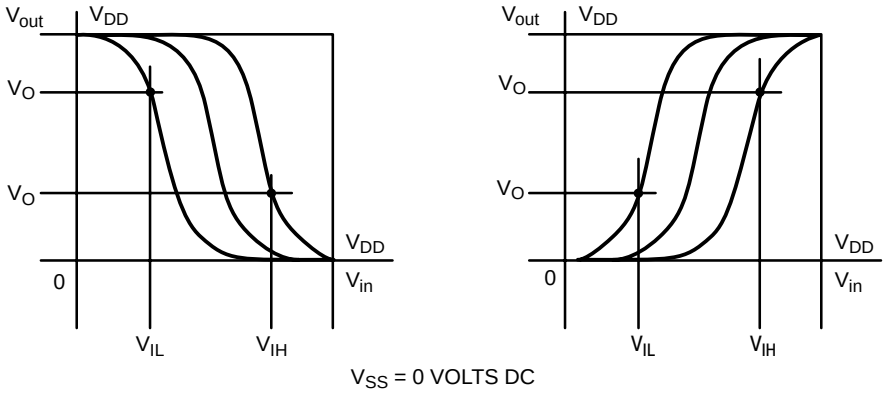
Figure 13. V_{DD} = 15 Vdc

DC NOISE MARGIN

The DC noise margin is defined as the input voltage range from an ideal “1” or “0” input level which does not produce output state change(s). The typical and guaranteed limit values of the input values V_{IL} and V_{IH} for the output(s) to be at a fixed voltage V_O are given in the Electrical Characteristics table. V_{IL} and V_{IH} are presented graphically in Figure 11.

Guaranteed minimum noise margins for both the “1” and “0” levels =

1.0 V with a 5.0 V supply
2.0 V with a 10.0 V supply
2.5 V with a 15.0 V supply

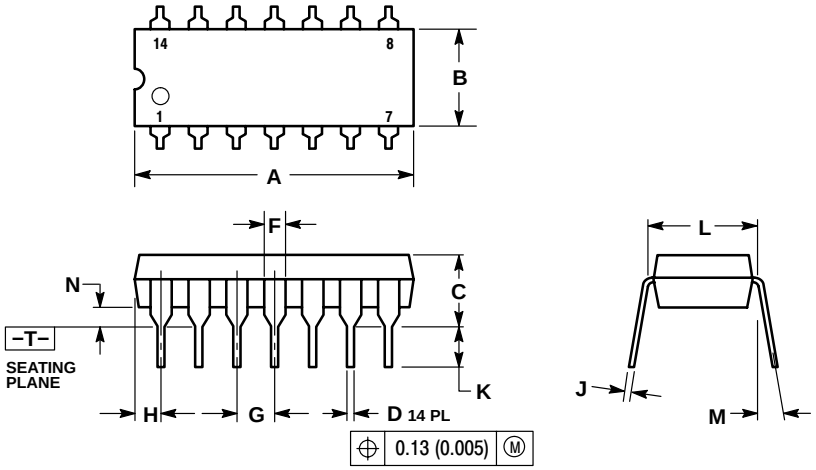


(a) Inverting Function **(b) Non−Inverting Function**

Figure 14. DC Noise Immunity

PACKAGE DIMENSIONS

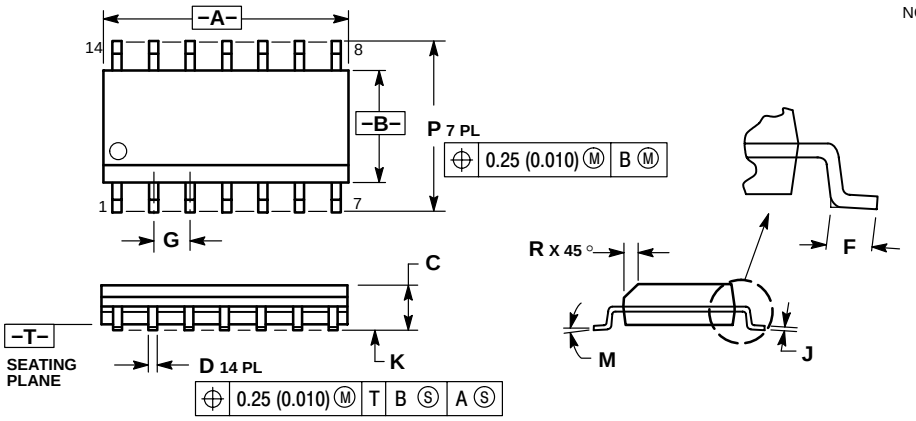
P SUFFIX
PLASTIC DIP PACKAGE
CASE 646−06
ISSUE N



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.715	0.770	18.16	18.80
B	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
H	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
M	−−−	10 °	−−−	10 °
N	0.015	0.039	0.38	1.01

D SUFFIX
PLASTIC SOIC PACKAGE
CASE 751A−03
ISSUE G

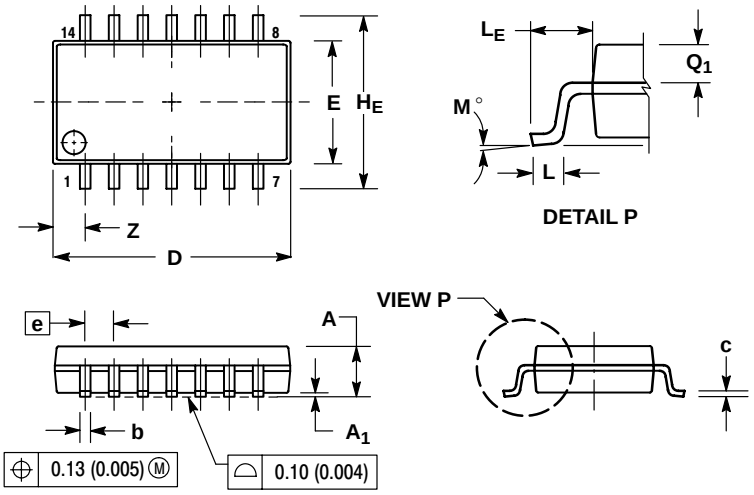


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7 °	0 °	7 °
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

F SUFFIX
PLASTIC EIAJ SOIC PACKAGE
CASE 965−01
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A_1	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H_E	7.40	8.20	0.291	0.323
0.50	0.50	0.85	0.020	0.033
L_E	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q_1	0.70	0.90	0.028	0.035
Z	---	1.42	---	0.056

PUBLICATION ORDERING INFORMATION

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